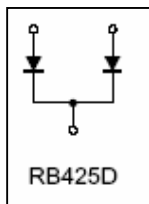


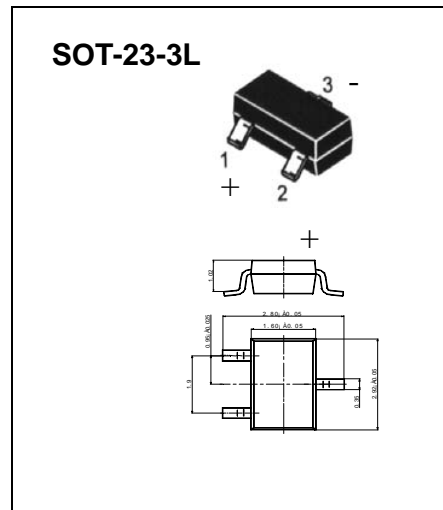
RB425D Schottky barrier Diodes

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability



Marking: D3L



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	40	V
Mean rectifying current	I _O	100	mA
Peak forward surge current	I _{FSM}	1	A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{F1}			0.55	V	I _F =100mA
	V _{F2}			0.34	V	I _F =10mA
Reverse current	I _R			30	μA	V _R =10V
Capacitance between terminals	C _T		6		pF	V _R =10V, f=1MHZ